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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	90
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	112-BGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg290f1024-bga112t

2.1.27 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSE[™]), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.28 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32GG290 to keep track of time and retain data, even if the main power source should drain out.

2.1.29 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.30 General Purpose Input/Output (GPIO)

In the EFM32GG290, there are 90 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32GG290 is a subset of the feature set described in the EFM32GG Reference Manual. Table 2.1 (p. 7) describes device specific implementation of the features.

Table 2.1. Configuration Summary

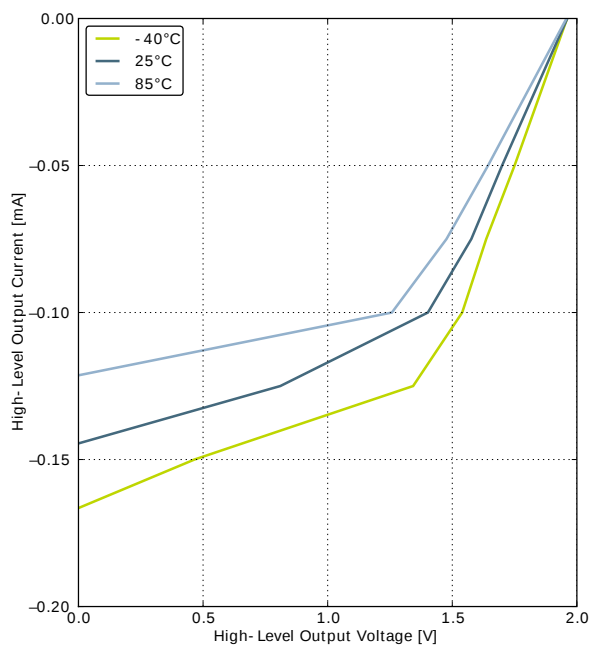
Module	Configuration	Pin Connections
Cortex-M3	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA

3.8 General Purpose Input Output

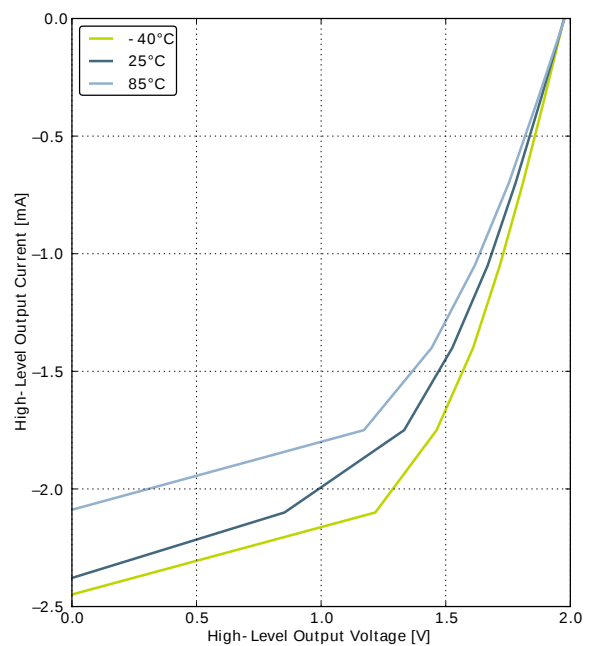
Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
V _{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
		Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
		Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
V _{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
		Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V

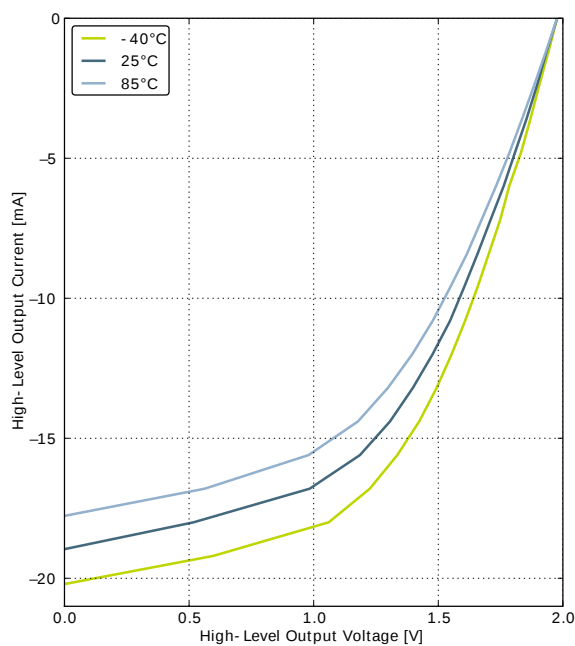
Figure 3.5. Typical High-Level Output Current, 2V Supply Voltage



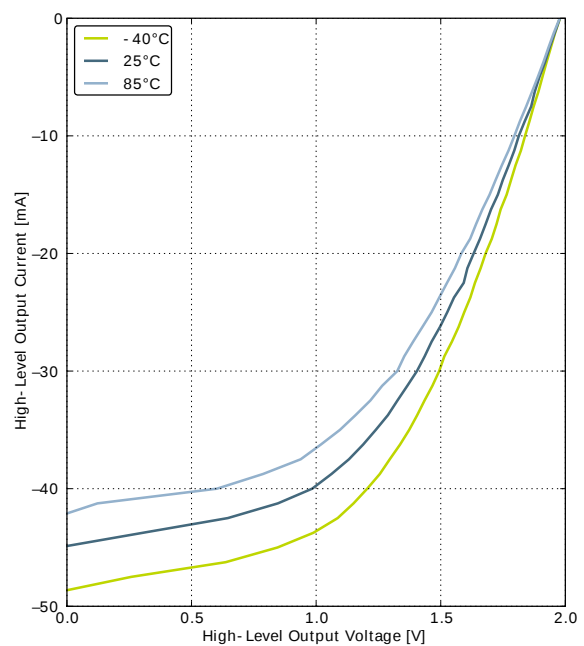
GPIO_Px_CTRL DRIVEMODE = LOWEST



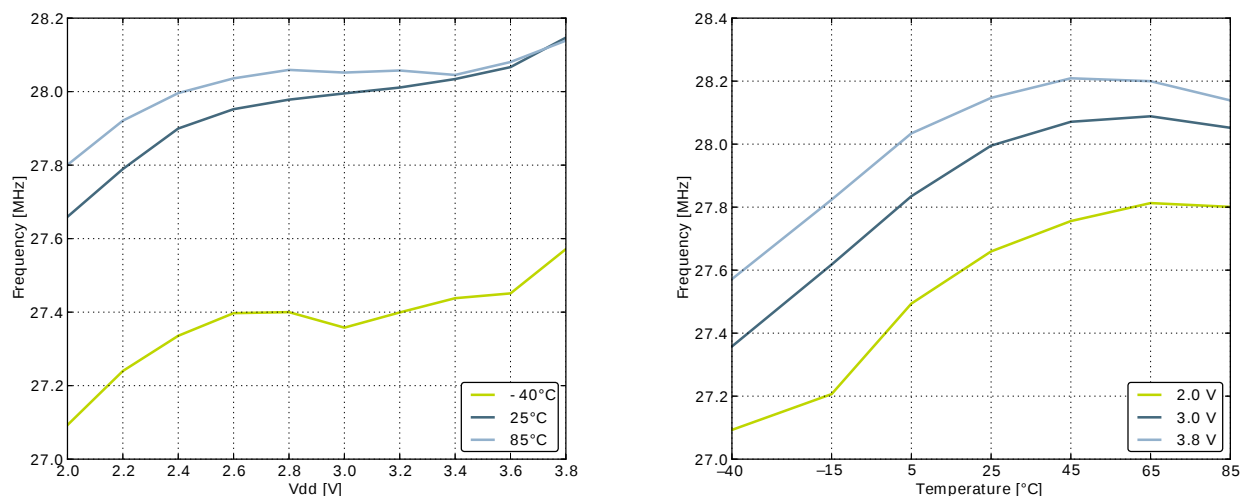
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.16. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature

3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{AUXHFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48 ¹	6.60 ¹	6.72 ¹	MHz
		1 MHz frequency band	1.15 ²	1.20 ²	1.25 ²	MHz
$t_{\text{AUXHFRCO_settling}}$	Settling time after start-up	$f_{\text{AUXHFRCO}} = 14 \text{ MHz}$		0.6		Cycles
$\text{DC}_{\text{AUXHFRCO}}$	Duty cycle	$f_{\text{AUXHFRCO}} = 14 \text{ MHz}$	48.5	50	51	%
$\text{TUNESTEP}_{\text{AUXHFRCO}}$	Frequency step for LSB change in TUNING value			0.3 ³		%

¹For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

²For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

³The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
GAIN _{ED}	Gain error drift	1.25V reference		0.01 ²	0.033 ³	%/°C
		2.5V reference		0.01 ²	0.03 ³	%/°C
OFFSET _{ED}	Offset error drift	1.25V reference		0.2 ²	0.7 ³	LSB/°C
		2.5V reference		0.2 ²	0.62 ³	LSB/°C

¹On the average every ADC will have one missing code, most likely to appear around 2048 +/- n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

²Typical numbers given by $\text{abs}(\text{Mean}) / (85 - 25)$.

³Max number given by $(\text{abs}(\text{Mean}) + 3 \times \text{stddev}) / (85 - 25)$.

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.17 (p. 32) and Figure 3.18 (p. 33) , respectively.

Figure 3.17. Integral Non-Linearity (INL)

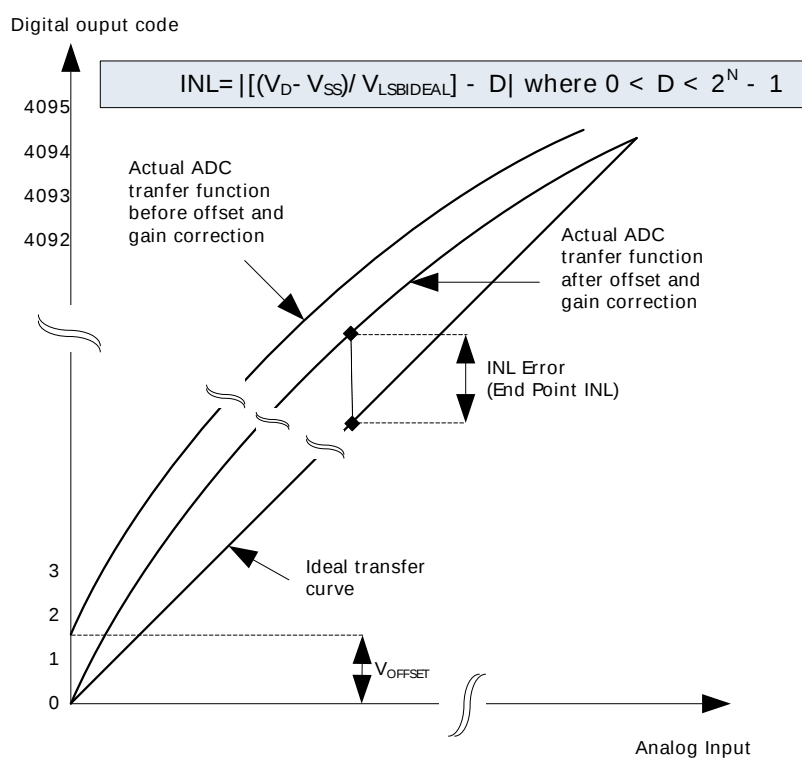


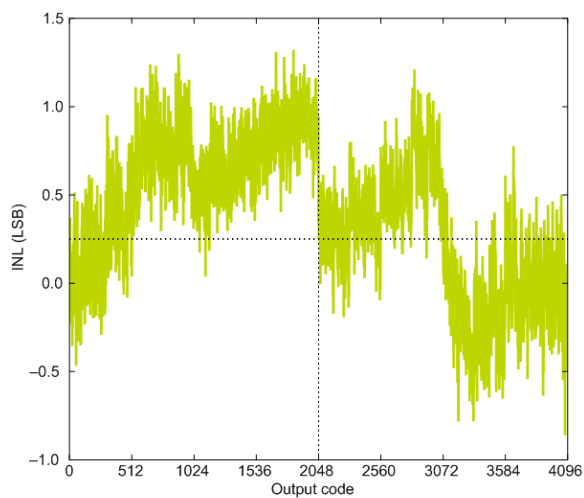
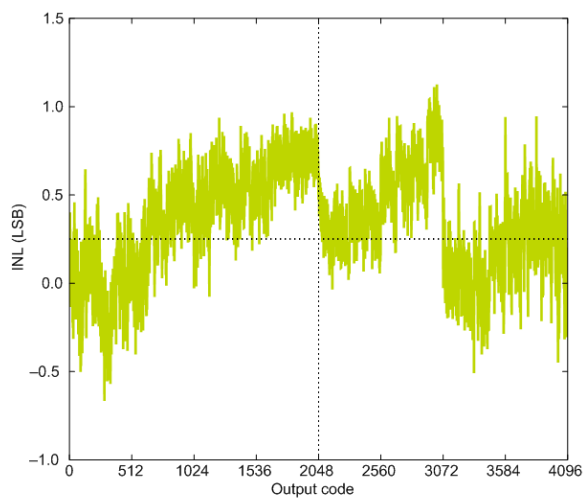
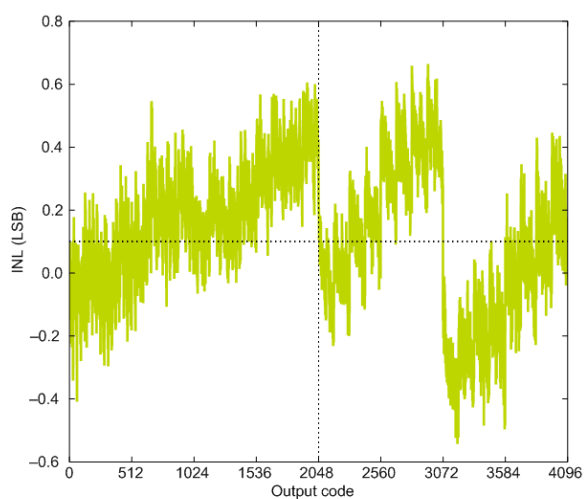
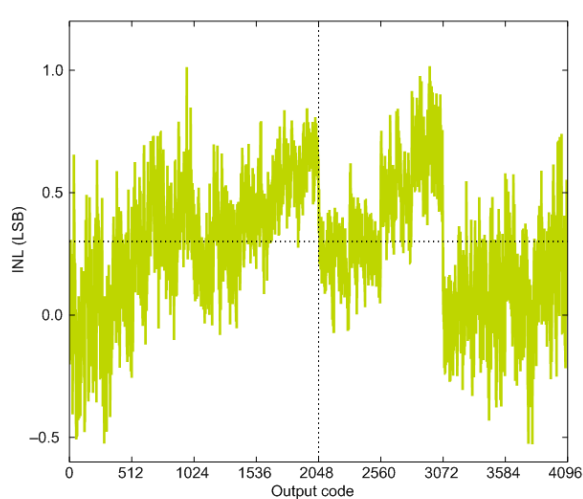
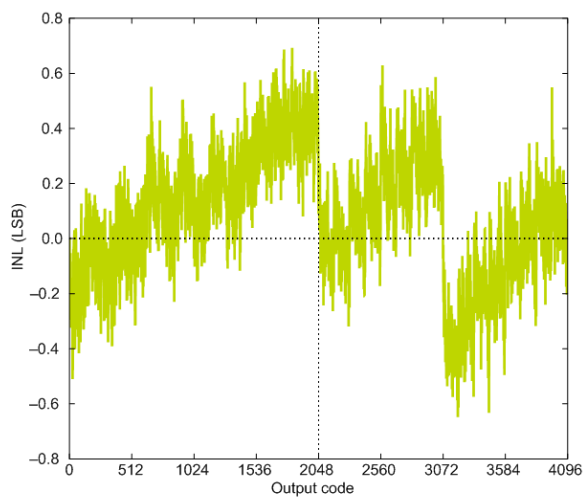
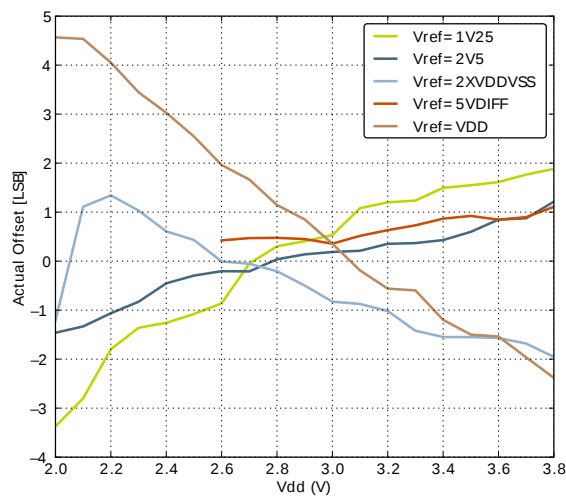
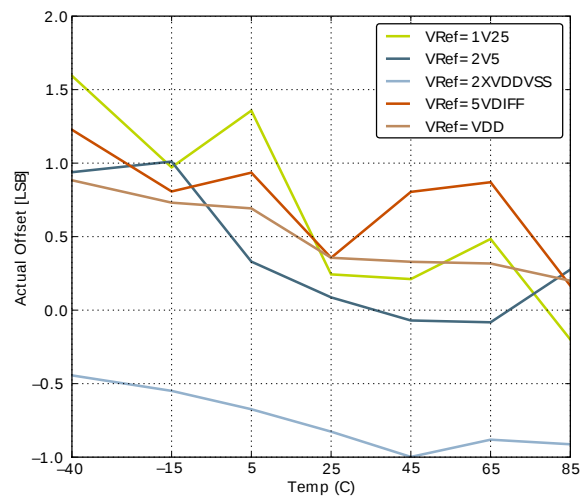
Figure 3.20. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C**1.25V Reference****2.5V Reference****2XVDDVSS Reference****5VDIFF Reference****VDD Reference**

Figure 3.22. ADC Absolute Offset, Common Mode = $V_{dd} / 2$

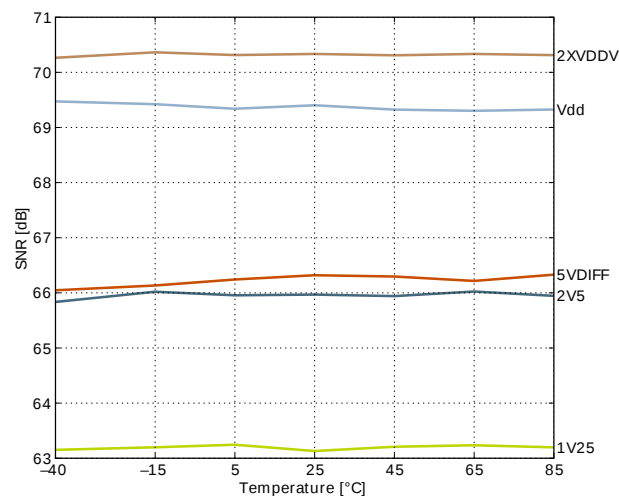


Offset vs Supply Voltage, Temp = 25°C

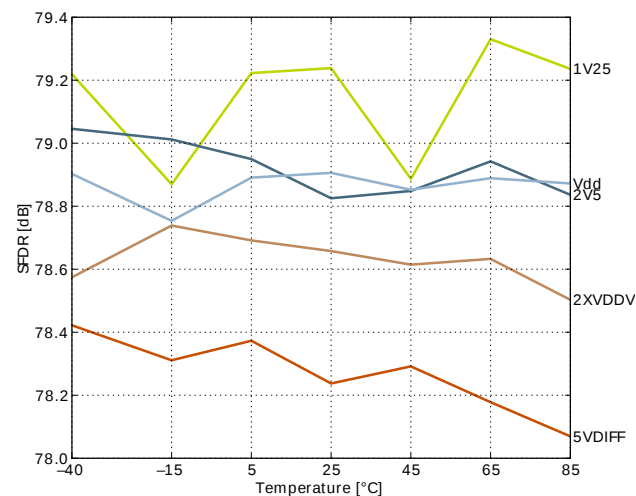


Offset vs Temperature, $V_{dd} = 3V$

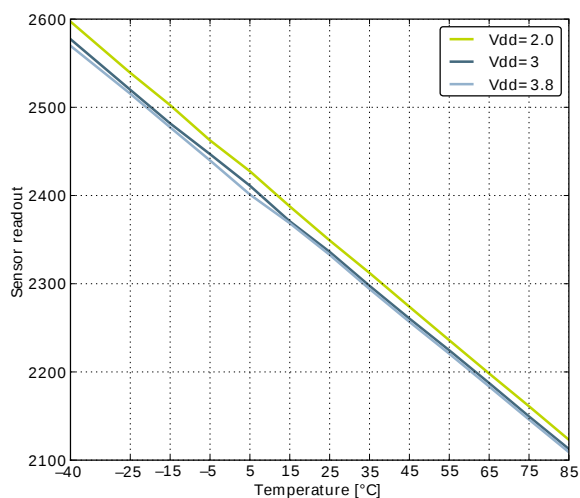
Figure 3.23. ADC Dynamic Performance vs Temperature for all ADC References, $V_{dd} = 3V$



Signal to Noise Ratio (SNR)



Spurious-Free Dynamic Range (SFDR)

Figure 3.24. ADC Temperature sensor readout

3.11 Digital Analog Converter (DAC)

Table 3.15. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
		VDD voltage reference, differential	$-V_{DD}$		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12 bit		400 ¹	600 ¹	μA
		100 kSamples/s, 12 bit		200 ¹	260 ¹	μA
		1 kSamples/s 12 bit NORMAL		17 ¹	25 ¹	μA
SR_{DAC}	Sample rate				500	ksamples/s
f_{DAC}	DAC clock frequency	Continuous Mode			1000	kHz
		Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
$CYC_{DACCONV}$	Clock cycles per conversion			2		
$t_{DACCONV}$	Conversion time		2			μs
$t_{DACSETTLE}$	Settling time			5		μs
SNR_{DAC}	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		58		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
SNDR _{DAC}	Signal to Noise-pulse Distortion Ratio (SNDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		56		dB
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
SFDR _{DAC}	Spurious-Free Dynamic Range(SFDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		61		dBc
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
V _{DACOFFSET}	Offset voltage	After calibration, single ended		2	12	mV
		After calibration, differential		2		mV
DNL _{DAC}	Differential non-linearity			±1		LSB
INL _{DAC}	Integral non-linearity			±5		LSB
MC _{DAC}	No missing codes			12		bits

¹ Measured with a static input code and no loading on the output.

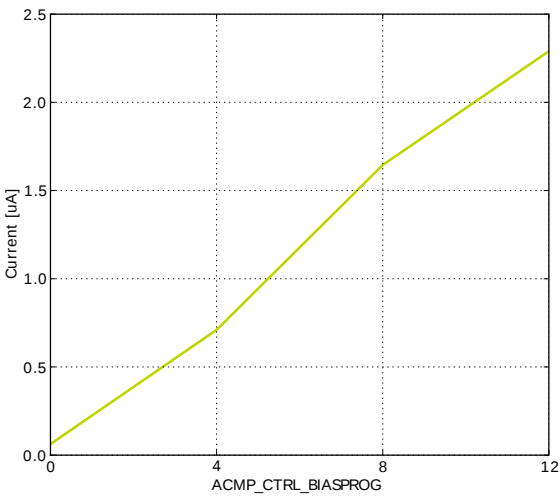
3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

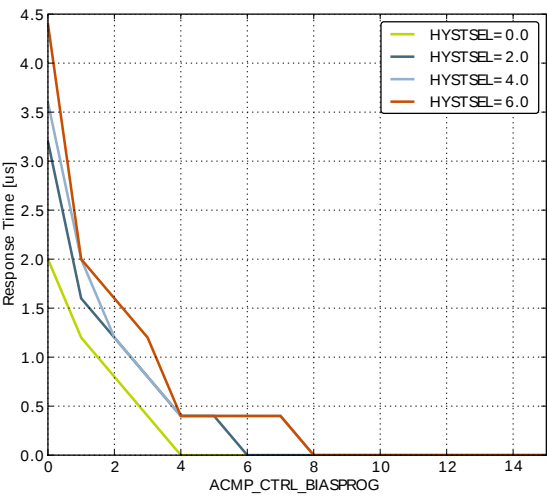
Table 3.16. OPAMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{OPAMP}	Active Current	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		350	405	μA
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	115	μA

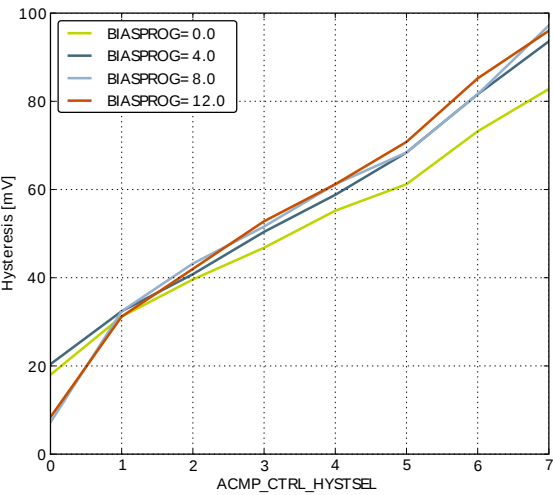
Figure 3.30. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



Current consumption, HYSTSEL = 4



Response time



Hysteresis

Table 3.19. EBI Write Enable Timing

Symbol	Parameter	Min	Typ	Max	Unit
$t_{OH_WEn}^{1\ 2\ 3\ 4}$	Output hold time, from trailing EBI_WEn/ EBI_NANDWEn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	$-6.00 + (WRHOLD * t_{HFCORECLK})$			ns
$t_{OSU_WEn}^{1\ 2\ 3\ 4\ 5}$	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_WEn/ EBI_NANDWEn edge	$-14.00 + (WRSETUP * t_{HFCORECLK})$			ns
$t_{WIDTH_WEn}^{1\ 2\ 3\ 4\ 5}$	EBI_WEn/EBI_NANDWEn pulse width	$-7.00 + ((WRSTRB + 1) * t_{HFCORECLK})$			ns

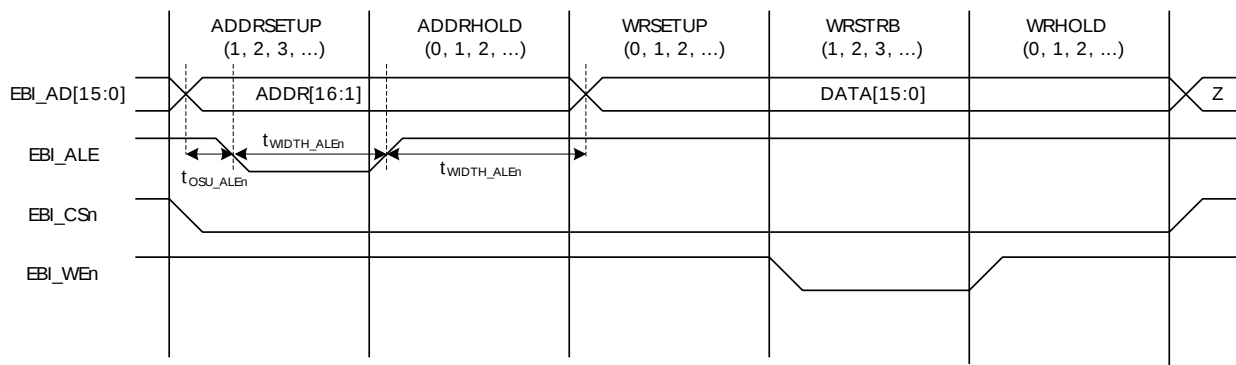
¹Applies for all addressing modes (figure only shows D16 addressing mode)

²Applies for both EBI_WEn and EBI_NANWEn (figure only shows EBI_WEn)

³Applies for all polarities (figure only shows active low signals)

⁴Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

⁵ The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFWE=0. The leading edge of EBI_WEn can be moved to the right by setting HALFWE=1. This decreases the length of t_{WIDTH_WEn} and increases the length of t_{OSU_WEn} by $1/2 * t_{HFCLKNODIV}$.

Figure 3.32. EBI Address Latch Enable Related Output Timing**Table 3.20. EBI Address Latch Enable Related Output Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{OH_ALEn}^{1\ 2\ 3\ 4}$	Output hold time, from trailing EBI_ALE edge to EBI_AD invalid	$-6.00 + (ADDRHOLD^5 * t_{HFCORECLK})$			ns
$t_{OSU_ALEn}^{1\ 2\ 4}$	Output setup time, from EBI_AD valid to leading EBI_ALE edge	$-13.00 + (0 * t_{HFCORECLK})$			ns
$t_{WIDTH_ALEn}^{1\ 2\ 3\ 4}$	EBI_ALEn pulse width	$-7.00 + (ADDRSETUP + 1) * t_{HFCORECLK}$			ns

¹Applies to addressing modes D8A24ALE and D16A16ALE (figure only shows D16A16ALE)

²Applies for all polarities (figure only shows active low signals)

³ The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFALE=0. The trailing edge of EBI_ALE can be moved to the left by setting HALFALE=1. This decreases the length of t_{WIDTH_ALEn} and increases the length of t_{OH_ALEn} by $t_{HFCORECLK} - 1/2 * t_{HFCLKNODIV}$.

⁴Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

⁵Figure only shows a write operation. For a multiplexed read operation the address hold time is controlled via the RDSETUP state instead of via the ADDRHOLD state.

Symbol	Parameter	Min	Typ	Max	Unit
$t_{H_ARDY}^{1\ 2\ 3\ 4}$	Hold time, from trailing EBI_REn, EBI_WEn edge to EBI_ARDY invalid		-1		ns

¹Applies for all addressing modes (figure only shows D16A8.)

²Applies for EBI_REn, EBI_WEn (figure only shows EBI_REn)

³Applies for all polarities (figure only shows active low signals)

⁴Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

3.16 I2C

Table 3.24. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		100 ¹	kHz
t_{LOW}	SCL clock low time	4.7			μs
t_{HIGH}	SCL clock high time	4.0			μs
$t_{SU,DAT}$	SDA set-up time	250			ns
$t_{HD,DAT}$	SDA hold time	8		3450 ^{2,3}	ns
$t_{SU,STA}$	Repeated START condition set-up time	4.7			μs
$t_{HD,STA}$	(Repeated) START condition hold time	4.0			μs
$t_{SU,STO}$	STOP condition set-up time	4.0			μs
t_{BUF}	Bus free time between a STOP and START condition	4.7			μs

¹For the minimum HPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32GG Reference Manual.

²The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

³When transmitting data, this number is guaranteed only when $I2Cn_CLKDIV < ((3450 \cdot 10^{-9} [s] \cdot f_{HPERCLK} [Hz]) - 4)$.

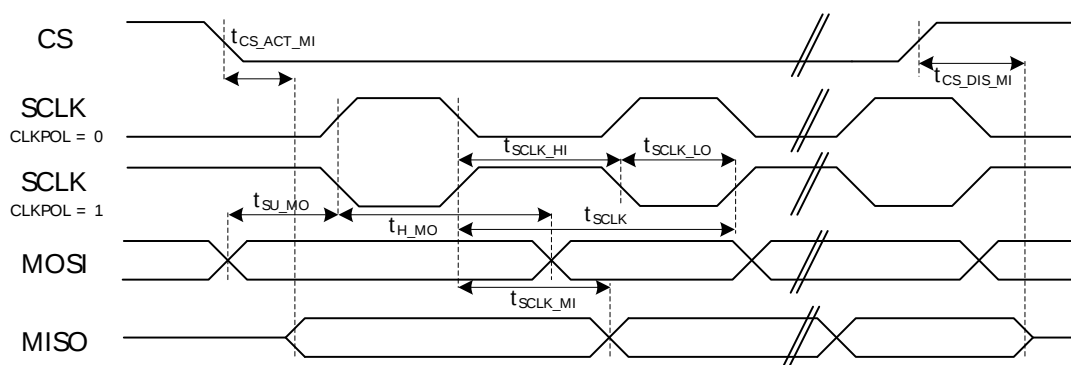
Table 3.25. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		400 ¹	kHz
t_{LOW}	SCL clock low time	1.3			μs
t_{HIGH}	SCL clock high time	0.6			μs
$t_{SU,DAT}$	SDA set-up time	100			ns
$t_{HD,DAT}$	SDA hold time	8		900 ^{2,3}	ns
$t_{SU,STA}$	Repeated START condition set-up time	0.6			μs
$t_{HD,STA}$	(Repeated) START condition hold time	0.6			μs
$t_{SU,STO}$	STOP condition set-up time	0.6			μs
t_{BUF}	Bus free time between a STOP and START condition	1.3			μs

¹For the minimum HPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32GG Reference Manual.

²The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

³When transmitting data, this number is guaranteed only when $I2Cn_CLKDIV < ((900 \cdot 10^{-9} [s] \cdot f_{HPERCLK} [Hz]) - 4)$.

Figure 3.37. SPI Slave Timing**Table 3.28. SPI Slave Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{SCLK_sl}^{1,2}$	SCKL period	$2 * t_{HFER-CLK}$			ns
$t_{SCLK_hi}^{1,2}$	SCLK high period	$3 * t_{HFER-CLK}$			ns
$t_{SCLK_lo}^{1,2}$	SCLK low period	$3 * t_{HFER-CLK}$			ns
$t_{CS_ACT_MI}^{1,2}$	CS active to MISO	4.00		30.00	ns
$t_{CS_DIS_MI}^{1,2}$	CS disable to MISO	4.00		30.00	ns
$t_{SU_MO}^{1,2}$	MOSI setup time	4.00			ns
$t_{H_MO}^{1,2}$	MOSI hold time	$2 + 2 * t_{HF-PERCLK}$			ns
$t_{SCLK_MI}^{1,2}$	SCLK to MISO	$9 + t_{HFER-CLK}$		$36 + 2 * t_{HF-PERCLK}$	ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

3.18 Digital Peripherals

Table 3.29. Digital Peripherals

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{USART}	USART current	USART idle current, clock enabled		4.9		$\mu A / MHz$
I_{UART}	UART current	UART idle current, clock enabled		3.4		$\mu A / MHz$
I_{LEUART}	LEUART current	LEUART idle current, clock enabled		140		nA
I_{I2C}	I2C current	I2C idle current, clock enabled		6.1		$\mu A / MHz$
I_{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		6.9		$\mu A / MHz$
$I_{LETIMER}$	LETIMER current	LETIMER idle current, clock enabled		119		nA

BGA112 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
						ETM_TD1 #3
D2	PA2		EBI_AD11 #0/1/2	TIM0_CC2 #0/1		CMU_CLK0 #0 ETM_TD0 #3
D3	PB15					ETM_TD2 #1
D4	VSS	Ground.				
D5	IOVDD_6	Digital IO power supply 6.				
D6	PD9		EBI_CS0 #0/1/2			
D7	IOVDD_5	Digital IO power supply 5.				
D8	PF1			TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 I2C0_SCL #5 LEU0_RX #3	DBG_SWDIO #0/1/2/3 GPIO_EM4WU3
D9	PE7		EBI_A14 #0/1/2		US0_TX #1	
D10	PC8	ACMP1_CH0	EBI_A15 #0/1/2	TIM2_CC0 #2	US0_CS #2	LES_CH8 #0
D11	PC9	ACMP1_CH1	EBI_A09 #1/2	TIM2_CC1 #2	US0_CLK #2	LES_CH9 #0 GPIO_EM4WU2
E1	PA6		EBI_AD15 #0/1/2		LEU1_RX #1	ETM_TCLK #3 GPIO_EM4WU1
E2	PA5		EBI_AD14 #0/1/2	TIM0_CDTI2 #0	LEU1_TX #1	LES_ALTEX4 #0 ETM_TD3 #3
E3	PA4		EBI_AD13 #0/1/2	TIM0_CDTI1 #0	U0_RX #2	LES_ALTEX3 #0 ETM_TD2 #3
E4	PB0		EBI_A16 #0/1/2	TIM1_CC0 #2		
E8	PF0			TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 I2C0_SDA #5 LEU0_TX #3	DBG_SWCLK #0/1/2/3
E9	PE0		EBI_A07 #0/1/2	TIM3_CC0 #1 PCNT0_S0IN #1	U0_TX #1 I2C1_SDA #2	
E10	PE1		EBI_A08 #0/1/2	TIM3_CC1 #1 PCNT0_S1IN #1	U0_RX #1 I2C1_SCL #2	
E11	PE3	BU_STAT	EBI_A10 #0		U1_RX #3	ACMP1_O #1
F1	PB1		EBI_A17 #0/1/2	TIM1_CC1 #2		
F2	PB2		EBI_A18 #0/1/2	TIM1_CC2 #2		
F3	PB3		EBI_A19 #0/1/2	PCNT1_S0IN #1	US2_TX #1	
F4	PB4		EBI_A20 #0/1/2	PCNT1_S1IN #1	US2_RX #1	
F8	VDD_DREG	Power supply for on-chip voltage regulator.				
F9	VSS_DREG	Ground for on-chip voltage regulator.				
F10	PE2	BU_VOUT	EBI_A09 #0	TIM3_CC2 #1	U1_TX #3	ACMP0_O #1
F11	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size C _{DECOUPLE} is required at this pin.				
G1	PB5		EBI_A21 #0/1/2		US2_CLK #1	
G2	PB6		EBI_A22 #0/1/2		US2_CS #1	
G3	VSS	Ground.				
G4	IOVDD_0	Digital IO power supply 0.				
G8	IOVDD_4	Digital IO power supply 4.				
G9	VSS	Ground.				
G10	PC6	ACMP0_CH6	EBI_A05 #0/1/2		I2C0_SDA #2 LEU1_TX #0	LES_CH6 #0 ETM_TCLK #2

BGA112 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
		To apply an external reset source to this pin, it is required to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.				
K7	AVSS_1	Analog ground 1.				
K8	AVDD_2	Analog power supply 2.				
K9	AVDD_1	Analog power supply 1.				
K10	AVSS_0	Analog ground 0.				
K11	PD1	ADC0_CH1 DAC0_OUT1ALT #4/ OPAMP_OUT1ALT		TIM0_CC0 #3 PCNT2_S1IN #0	US1_RX #1	DBG_SWO #2
L1	PB8	LFXTAL_N		TIM1_CC1 #3	US0_RX #4 US1_CS #0	
L2	PC5	ACMP0_CH5 OPAMP_N0	EBI_NANDWE# #0/1/2	LETIM0_OUT1 #3 PCNT1_S1IN #0	US2_CS #0 I2C1_SCL #0	LES_CH5 #0
L3	PA14		EBI_A02 #0/1/2	TIM2_CC2 #1		
L4	IOVDD_1	Digital IO power supply 1.				
L5	PB11	DAC0_OUT0 / OPAMP_OUT0		LETIM0_OUT0 #1 TIM1_CC2 #3	I2C1_SDA #1	
L6	PB12	DAC0_OUT1 / OPAMP_OUT1		LETIM0_OUT1 #1	I2C1_SCL #1	
L7	AVSS_2	Analog ground 2.				
L8	PB13	HFXTAL_P			US0_CLK #4/5 LEU0_TX #1	
L9	PB14	HFXTAL_N			US0_CS #4/5 LEU0_RX #1	
L10	AVDD_0	Analog power supply 0.				
L11	PD0	ADC0_CH0 DAC0_OUT0ALT #4/ OPAMP_OUT0ALT OPAMP_OUT2 #1		PCNT2_S0IN #0	US1_TX #1	

4.2 Alternate Functionality Pinout

A wide selection of alternate functionality is available for multiplexing to various pins. This is shown in Table 4.2 (p. 57). The table shows the name of the alternate functionality in the first column, followed by columns showing the possible LOCATION bitfield settings.

Note

Some functionality, such as analog interfaces, do not have alternate settings or a LOCATION bitfield. In these cases, the pinout is shown in the column corresponding to LOCATION 0.

Table 4.2. Alternate functionality overview

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
ACMP0_CH0	PC0							Analog comparator ACMP0, channel 0.
ACMP0_CH1	PC1							Analog comparator ACMP0, channel 1.
ACMP0_CH2	PC2							Analog comparator ACMP0, channel 2.
ACMP0_CH3	PC3							Analog comparator ACMP0, channel 3.

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
EBI_AD03	PE11	PE11	PE11					External Bus Interface (EBI) address and data input / output pin 03.
EBI_AD04	PE12	PE12	PE12					External Bus Interface (EBI) address and data input / output pin 04.
EBI_AD05	PE13	PE13	PE13					External Bus Interface (EBI) address and data input / output pin 05.
EBI_AD06	PE14	PE14	PE14					External Bus Interface (EBI) address and data input / output pin 06.
EBI_AD07	PE15	PE15	PE15					External Bus Interface (EBI) address and data input / output pin 07.
EBI_AD08	PA15	PA15	PA15					External Bus Interface (EBI) address and data input / output pin 08.
EBI_AD09	PA0	PA0	PA0					External Bus Interface (EBI) address and data input / output pin 09.
EBI_AD10	PA1	PA1	PA1					External Bus Interface (EBI) address and data input / output pin 10.
EBI_AD11	PA2	PA2	PA2					External Bus Interface (EBI) address and data input / output pin 11.
EBI_AD12	PA3	PA3	PA3					External Bus Interface (EBI) address and data input / output pin 12.
EBI_AD13	PA4	PA4	PA4					External Bus Interface (EBI) address and data input / output pin 13.
EBI_AD14	PA5	PA5	PA5					External Bus Interface (EBI) address and data input / output pin 14.
EBI_AD15	PA6	PA6	PA6					External Bus Interface (EBI) address and data input / output pin 15.
EBI_ALE	PF3	PC11	PC11					External Bus Interface (EBI) Address Latch Enable output.
EBI_ARDY	PF2	PF2	PF2					External Bus Interface (EBI) Hardware Ready Control input.
EBI_BLO	PF6	PF6	PF6					External Bus Interface (EBI) Byte Lane/Enable pin 0.
EBI_BL1	PF7	PF7	PF7					External Bus Interface (EBI) Byte Lane/Enable pin 1.
EBI_CS0	PD9	PD9	PD9					External Bus Interface (EBI) Chip Select output 0.
EBI_CS1	PD10	PD10	PD10					External Bus Interface (EBI) Chip Select output 1.
EBI_CS2	PD11	PD11	PD11					External Bus Interface (EBI) Chip Select output 2.
EBI_CS3	PD12	PD12	PD12					External Bus Interface (EBI) Chip Select output 3.
EBI_CSTFT	PA7	PA7	PA7					External Bus Interface (EBI) Chip Select output TFT.
EBI_DCLK	PA8	PA8	PA8					External Bus Interface (EBI) TFT Dot Clock pin.
EBI_DTEN	PA9	PA9	PA9					External Bus Interface (EBI) TFT Data Enable pin.
EBI_HSNCR	PA11	PA11	PA11					External Bus Interface (EBI) TFT Horizontal Synchronization pin.
EBI_NANDREN	PC3	PC3	PC3					External Bus Interface (EBI) NAND Read Enable output.
EBI_NANDWEN	PC5	PC5	PC5					External Bus Interface (EBI) NAND Write Enable output.
EBI_REN	PF5	PF9	PF5					External Bus Interface (EBI) Read Enable output.
EBI_VSNCR	PA10	PA10	PA10					External Bus Interface (EBI) TFT Vertical Synchronization pin.
EBI_WEN	PF4	PF8	PF4					External Bus Interface (EBI) Write Enable output.
ETM_TCLK	PD7	PF8	PC6	PA6				Embedded Trace Module ETM clock .
ETM_TD0	PD6	PF9	PC7	PA2				Embedded Trace Module ETM data 0.
ETM_TD1	PD3	PD13	PD3	PA3				Embedded Trace Module ETM data 1.
ETM_TD2	PD4	PB15	PD4	PA4				Embedded Trace Module ETM data 2.

5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. BGA112 PCB Land Pattern

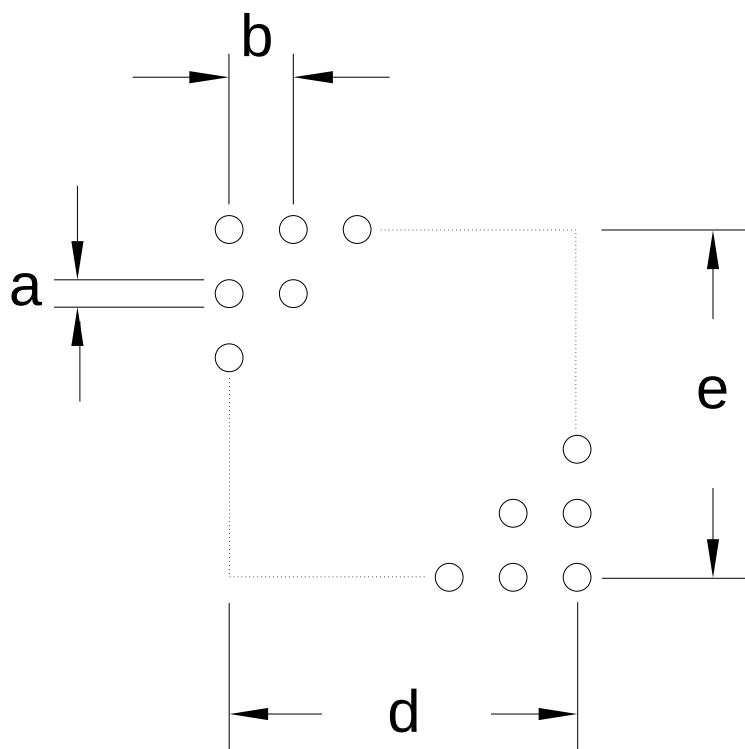


Table 5.1. BGA112 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.35
b	0.80
d	8.00
e	8.00

7 Revision History

7.1 Revision 1.40

March 21st, 2016

Added clarification on conditions for INL_{ADC} and DNL_{ADC} parameters.

Reduced maximum and typical current consumption for all EM0 entries except 48 MHz in the Current Consumption table in the Electrical Characteristics section.

Increased maximum specifications for EM2 current, EM3 current, and EM4 current in the Current Consumption table in the Electrical Characteristics section.

Increased typical specification for EM2 and EM3 current at 85 C in the Current Consumption table in the Electrical Characteristics section.

Added EM2, EM3, and EM4 current consumption vs. temperature graphs.

Added a new EM2 entry and specified the existing specification is for EM0 for the BOD threshold on falling external supply voltage in the Power Management table in the Electrical Characteristics section.

Reduced maximum input leakage current in the GPIO table in the Electrical Characteristics section.

Added a maximum current consumption specification to the LFRCO table in the Electrical Characteristics section.

Added maximum specifications for the active current including references for two channels to the DAC table in the Electrical Characteristics section.

Increased the maximum specification for DAC offset voltage in the DAC table in the Electrical Characteristics section.

Increased the typical specifications for active current with $FULLBIAS=1$ and capacitive sense internal resistance in the ACMP table in the Electrical Characteristics section.

Added minimum and maximum specifications and updated the typical value for the VCMP offset voltage in the VCMP table in the Electrical Characteristics section.

Removed the maximum specification and reduced the typical value for hysteresis in the VCMP table in the Electrical Characteristics section.

Updated all graphs in the Electrical Characteristics section to display data for 2.0 V as the minimum voltage.

7.2 Revision 1.30

May 23rd, 2014

Removed "preliminary" markings

Updated HFRCO figures.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated Current Consumption information.

Updated Power Management information.

7.10 Revision 0.91

March 21th, 2011

Added new alternative locations for EBI and SWO.

Corrected slew rate data for Opamps.

7.11 Revision 0.90

February 4th, 2011

Initial preliminary release.

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